

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) Max}$	$I_{D Max}$ $T_A = +25^{\circ}C$
30V	18mΩ @ $V_{GS} = 10V$	7.5A
	28mΩ @ $V_{GS} = 4.5V$	6.1A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

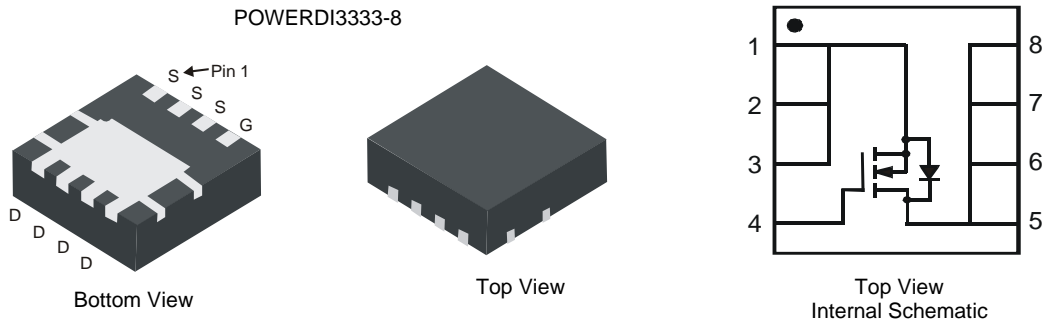
- Backlighting
- Power Management Functions
- DC-DC Converters

Features

- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% Unclamped Inductive Switch (UIS) test in production
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: POWERDI3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.072 grams (approximate)

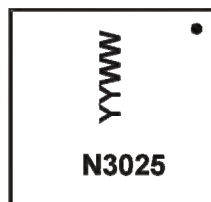


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3025LFG-7	POWERDI3333-8	2000/Tape & Reel
DMN3025LFG-13	POWERDI3333-8	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



N3025 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last digit of year (ex: 11 = 2011)
 WW = Week code (01 ~ 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	30	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	I _D	T _A = +25°C	7.5
		T _A = +70°C	6.1
	I _D	T _A = +25°C	10
		T _A = +70°C	7.8
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	2.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	60	A
Avalanche Current (Note 6) L = 0.1mH	I _{AR}	14	A
Avalanche Energy (Note 6) L = 0.1mH	E _{AR}	10	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	T _A = +25°C	2.0
		T _A = +70°C	1.3
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady State	61
		t < 10s	37
Thermal Resistance, Junction to Case	R _{θJC}	6.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±1	µA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.8	—	2.0	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	14	18	mΩ	V _{GS} = 10V, I _D = 7.8A
		—	23	28		V _{GS} = 4.5V, I _D = 7.0A
Forward Transfer Admittance	Y _{fs}	—	9	-	S	V _{DS} = 10V, I _D = 7.8A
Diode Forward Voltage	V _{SD}	—	0.70	1.0	V	V _{GS} = 0V, I _S = 6.3A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	605	—	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	74	—		
Reverse Transfer Capacitance	C _{rss}	—	58	—		
Gate resistance	R _g	—	1.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	5.3	—	nC	V _{DS} = 15V, I _D = 7.8A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	11.6	—		
Gate-Source Charge	Q _{gs}	—	2	—		
Gate-Drain Charge	Q _{gd}	—	2.4	—		
Turn-On Delay Time	t _{D(on)}	—	3.8	—	ns	V _{DD} = 15V, V _{GS} = 4.5V, R _L = 2.4Ω, R _G = 1Ω,
Turn-On Rise Time	t _r	—	4.1	—		
Turn-Off Delay Time	t _{D(off)}	—	17.9	—		
Turn-Off Fall Time	t _f	—	4.7	—		
Reverse Recovery Time	t _{rr}	—	5.5	—	ns	I _F = 12A, di/dt = 500A/µs
Reverse Recovery Charge	Q _{rr}	—	2.6	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1 inch square copper plate.
 - I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = +25°C
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

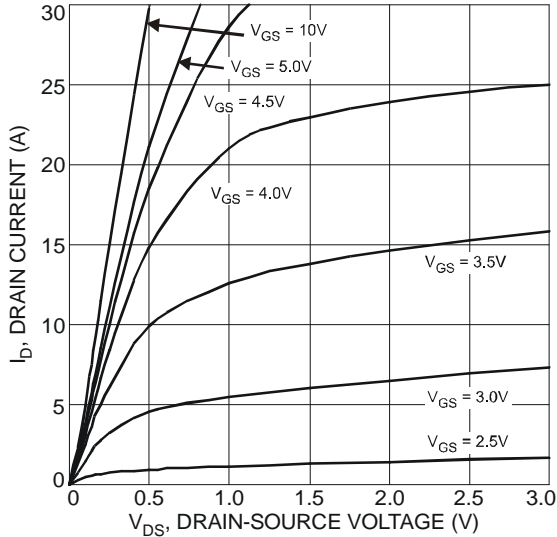


Figure 1 Typical Output Characteristic

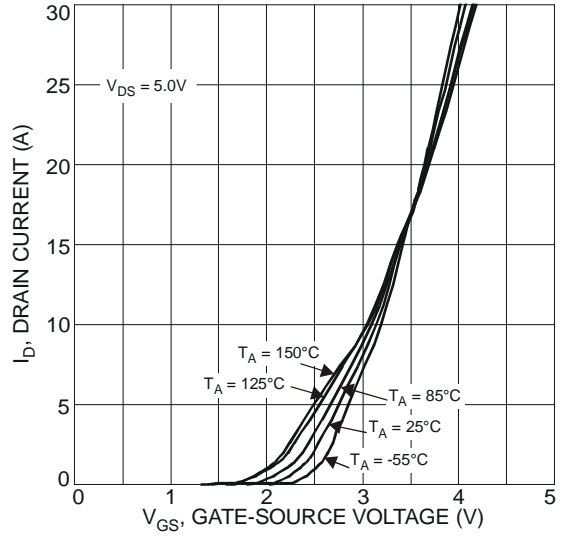


Figure 2 Typical Transfer Characteristics

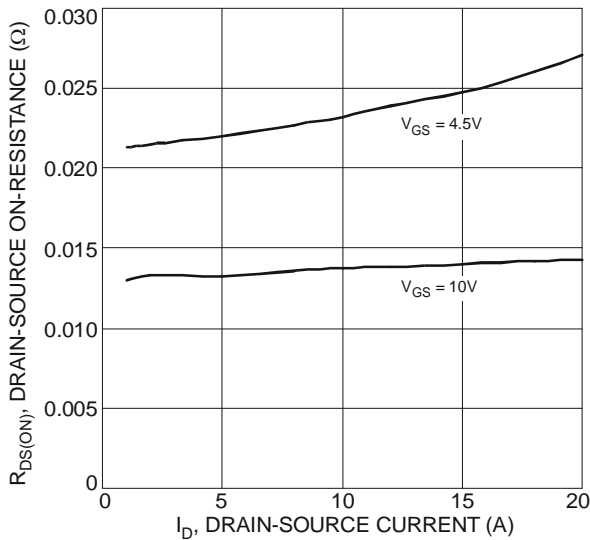


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

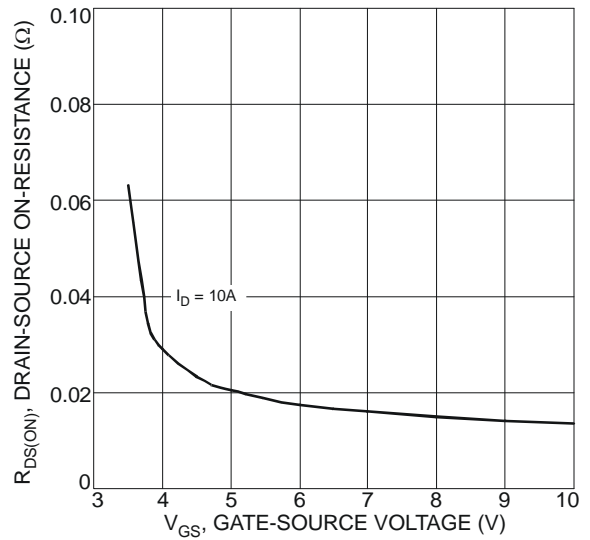


Figure 4 Typical On-Resistance vs. Drain Current and Gate Voltage

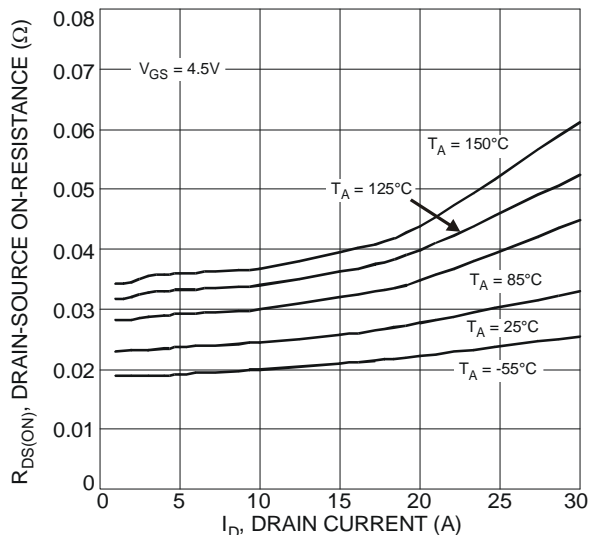


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

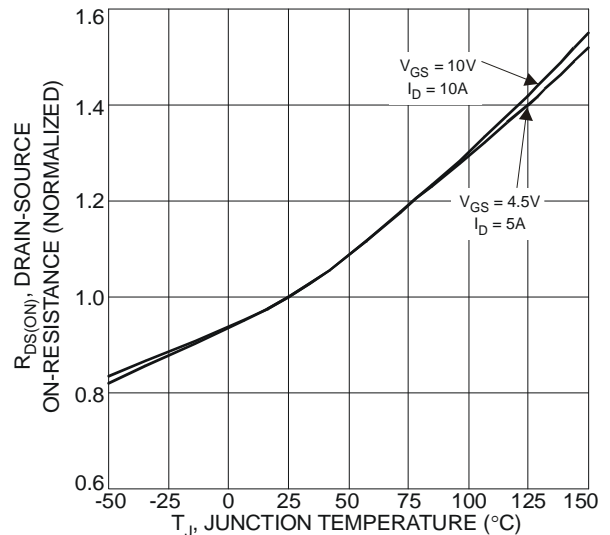


Figure 6 On-Resistance Variation with Temperature

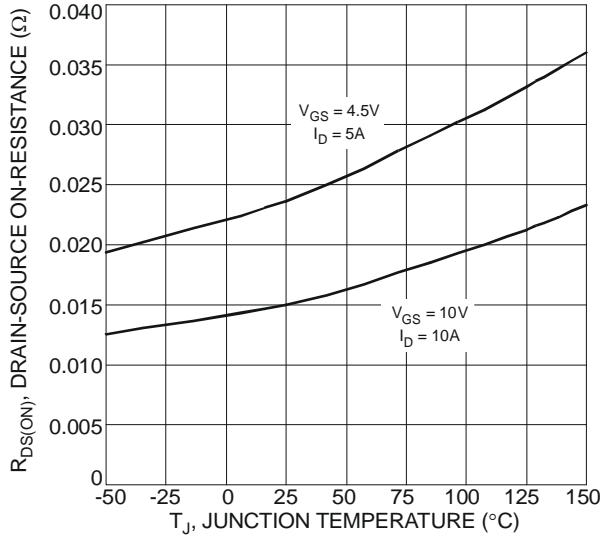


Figure 7 On-Resistance Variation with Temperature

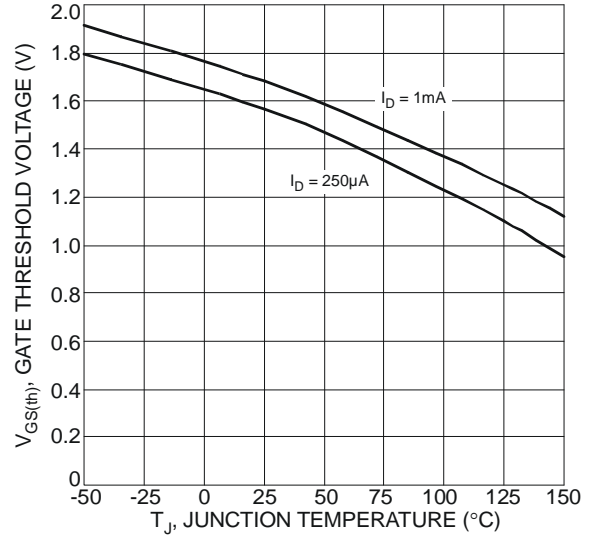


Figure 8 Gate Threshold Variation vs. Ambient Temperature

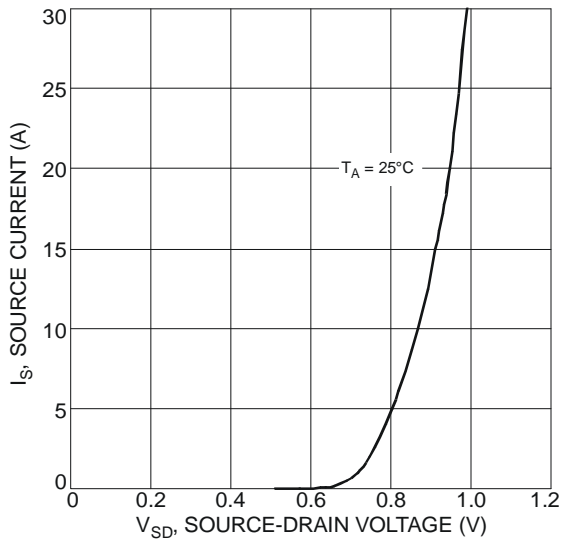


Figure 9 Diode Forward Current vs. Current

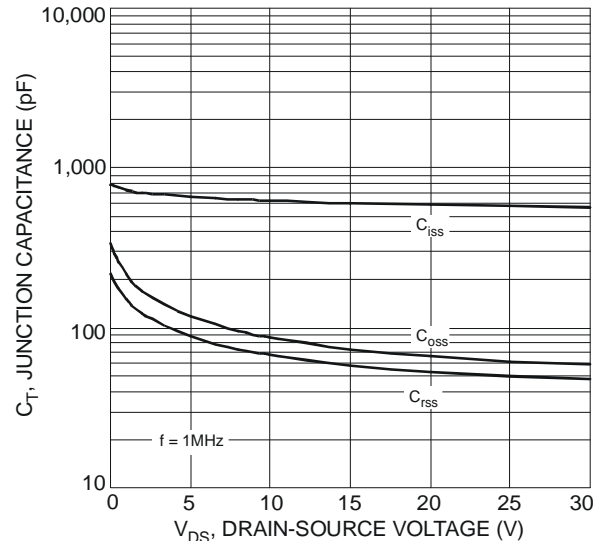


Figure 10 Typical Junction Capacitance

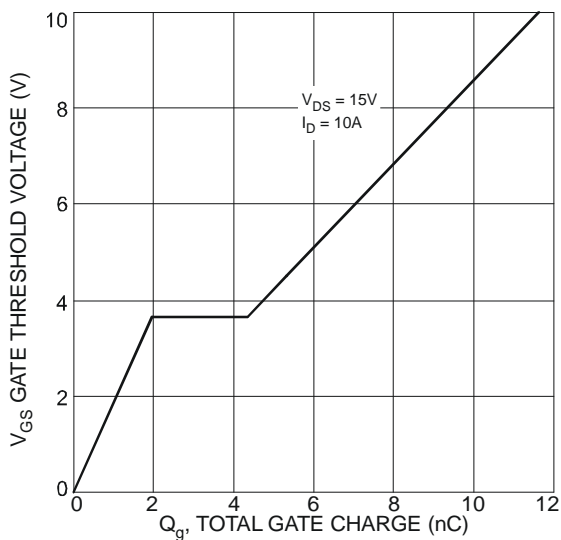


Figure 11 Gate Charge

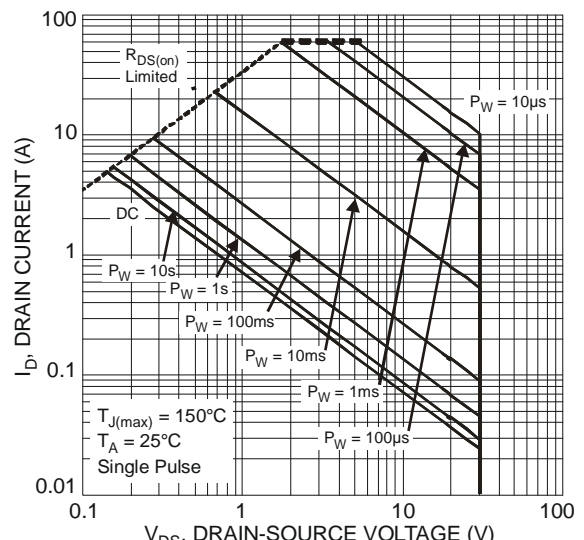


Figure 12 SOA, Safe Operation Area

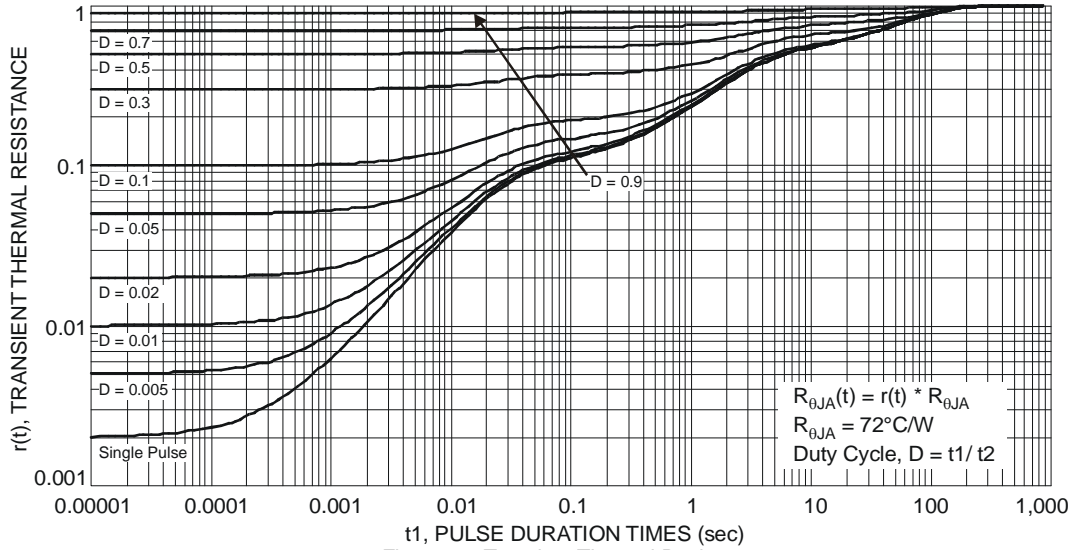
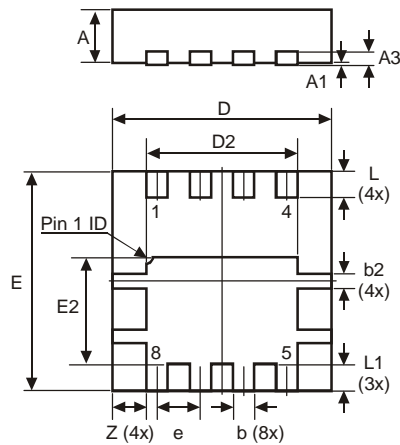


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.

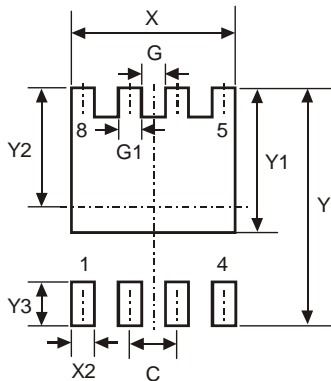


POWERDI3333-8			
Dim	Min	Max	Typ
D	3.25	3.35	3.30
E	3.25	3.35	3.30
D2	2.22	2.32	2.27
E2	1.56	1.66	1.61
A	0.75	0.85	0.80
A1	0	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
L	0.35	0.45	0.40
L1	-	-	0.39
e	-	-	0.65
Z	-	-	0.515

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.650
G	0.230
G1	0.420
Y	3.700
Y1	2.250
Y2	1.850
Y3	0.700
X	2.370
X2	0.420

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